

Day : Monday
Date: 6/27/2005
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Inventor Name Search Result

Your Search was:

Last Name = LIU

First Name = AI-SEN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 15
11048073	Not Issued	030	02/01/2005	SIOC PROPERTIES AND ITS UNIFORMITY IN BULK FOR DAMASCENE APPLICATIONS	LIU, AI-SEN
10872238	Not Issued	030	06/18/2004	MICRO-ETCHING METHOD TO REPLICATE ALIGNMENT MARKS FOR SEMICONDUCTOR WAFER PHOTOLITHOGRAPHY	LIU, AI-SEN
10833720	6884149	150	04/27/2004	METHOD AND SYSTEM FOR IN-SITU MONITORING OF MIXING RATIO OF HIGH SELECTIVITY SLURRY	LIU, AI-SEN
10764608	Not Issued	092	01/26/2004	METHOD FOR DISSOCIATING METALS FROM METAL COMPOUNDS	LIU, AI-SEN
10723236	Not Issued	041	11/26/2003	ADVANCED PROCESS CONTROL APPROACH FOR CU INTERCONNECT WIRING SHEET RESISTANCE CONTROL	LIU, AI-SEN
10692030	Not Issued	094	10/23/2003	SIOC PROPERTIES AND ITS UNIFORMITY IN BULK FOR DAMASCENE APPLICATIONS	LIU, AI-SEN
10687713	Not Issued	030	10/17/2003	SURFACE TREATED LOW-K DIELECTRIC AS DIFFUSION BARRIER FOR COPPER METALLIZATION	LIU, AI-SEN
10657847	Not Issued	071	09/09/2003	METHOD FOR FORMING DIELECTRIC BARRIER LAYER IN DAMASCENE STRUCTURE	LIU, AI-SEN
10439358	Not Issued	092	05/16/2003	SURFACE TREATMENT OF METAL INTERCONNECT LINES	LIU, AI-SEN
10435009	Not Issued	041	05/09/2003	METHOD FOR MULTIPLE SPACER WIDTH CONTROL	LIU, AI-SEN
10408689	Not Issued	092	04/07/2003	SELECTIVE SPACER LAYER DEPOSITION METHOD FOR FORMING SPACERS WITH DIFFERENT WIDTHS	LIU, AI-SEN
10369992	6746900	150	02/19/2003	METHOD FOR FORMING A SEMICONDUCTOR DEVICE HAVING HIGH-K GATE DIELECTRIC MATERIAL	LIU, AI-SEN

10323376	Not Issued	092	12/18/2002	METHOD FOR REWORKING A LITHOGRAPHIC PROCESS TO PROVIDE AN UNDAMAGED AND RESIDUE FREE ARC LAYER	LIU, AI-SEN
10322198	6895360	150	12/17/2002	METHOD TO MEASURE OXIDE THICKNESS BY FTIR TO IMPROVE AN IN-LINE CMP ENDPOINT DETERMINATION	LIU, AI-SEN
10170674	6729935	150	06/13/2002	METHOD AND SYSTEM FOR IN-SITU MONITORING OF MIXING RATIO OF HIGH SELECTIVITY SLURRY	LIU, AI-SEN

Inventor Search Completed: No Records to Display.

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Inventor Name Search Result

Your Search was:

Last Name = JANG

First Name = SYUN-MING

Application#	Patent#	Status	Date Filed	Title	Inventor Name 50
60631744	Not Issued	020	11/30/2004	METHOD FOR DECREASING A DIELECTRIC CONSTANT OF A LOW-K FILM	JANG, SYUN-MING
11091307	Not Issued	030	03/28/2005	BEOL INTEGRATION SCHEME FOR ETCHING DAMAGE FREE ELK	JANG, SYUN-MING
11084494	Not Issued	030	03/18/2005	METHOD OF ENHANCING ADHESION BETWEEN DIELECTRIC LAYERS	JANG, SYUN-MING
11082517	Not Issued	030	03/17/2005	SCRATCH REDUCTION FOR CHEMICAL MECHANICAL POLISHING	JANG, SYUN-MING
11048073	Not Issued	030	02/01/2005	SIOC PROPERTIES AND ITS UNIFORMITY IN BULK FOR DAMASCENE APPLICATIONS	JANG, SYUN-MING
11044929	Not Issued	020	01/27/2005	CONTACT STRUCTURE FORMED USING SUPERCRITICAL CLEANING FLUID AND ALCVD	JANG, SYUN-MING
10975238	Not Issued	020	10/28/2004	HETEROGENEOUS LOW K DIELECTRIC	JANG, SYUN-MING
10170840	6734079	150	06/13/2002	MICROELECTRONIC FABRICATION HAVING SIDEWALL PASSIVATED MICROELECTRONIC CAPACITOR STRUCTURE FABRICATED THEREIN	JANG, SYUN-MING
10170674	6729935	150	06/13/2002	METHOD AND SYSTEM FOR IN-SITU MONITORING OF MIXING RATIO OF HIGH SELECTIVITY SLURRY	JANG, SYUN-MING
10170242	6727172	150	06/12/2002	NOVEL PROCESS TO REDUCE CHEMICAL MECHANICAL POLISHING DAMAGE OF NARROW COPPER LINES	JANG, SYUN-MING
10140728	Not Issued	061	05/07/2002	METHOD FOR ACHIEVING UNIFORM CU CMP POLISHING	JANG, SYUN-MING
10139976	Not Issued	071	05/06/2002	METHOD FORMING COPPER CONTAINING SEMICONDUCTOR FEATURES TO PREVENT THERMALLY INDUCED DEFECTS	JANG, SYUN-MING
10131713	6812043	150	04/25/2002	METHOD FOR FORMING A CARBON DOPED OXIDE LOW-K INSULATING	JANG, SYUN-MING

				LAYER	
<u>10126417</u>	<u>6867135</u>	150	04/19/2002	VIA BOTTOM COPPER/BARRIER INTERFACE IMPROVEMENT TO RESOLVE VIA ELECTROMIGRATION AND STRESS MIGRATION	JANG, SYUN-MING
<u>10102574</u>	<u>6908773</u>	150	03/19/2002	ATR-FTIR METAL SURFACE CLEANLINESS MONITORING	JANG, SYUN-MING
<u>10074887</u>	Not Issued	071	02/12/2002	FORMULATION OF ULTRA LOW-K INSULATOR USING SELECTIVE RADICAL REACTION	JANG, SYUN-MING
<u>10072244</u>	<u>6686284</u>	150	02/06/2002	CHEMICAL MECHANICAL POLISHER EQUIPPED WITH CHILLED RETAINING RING AND METHOD OF USING	JANG, SYUN-MING
<u>10062314</u>	Not Issued	094	02/01/2002	HARD MASKING METHOD FOR FORMING PATTERNED OXYGEN CONTAINING PLASMA ETCHABLE LAYER	JANG, SYUN-MING
<u>09435678</u>	<u>6174797</u>	150	11/08/1999	SILICON OXIDE DIELECTRIC MATERIAL WITH EXCESS SILICON AS DIFFUSION BARRIER LAYER	JANG, SYUN-MING
<u>09431150</u>	<u>6417106</u>	150	11/01/1999	UNDERLAYER LINER FOR COPPER DAMASCENCE IN LOW K DIELECTRIC	JANG, SYUN-MING
<u>09425902</u>	Not Issued	083	10/25/1999	THERMAL ANNEALING METHOD FOR REDUCTION OF HOT CARRIER DEGRADATION OF DIELECTRIC PASSIVATION LAYER	JANG, SYUN-MING
<u>09421517</u>	<u>6559040</u>	150	10/20/1999	PROCESS FOR POLISHING THE TOP SURFACE OF A POLYSILICON GATE	JANG, SYUN-MING
<u>09421511</u>	<u>6090696</u>	150	10/20/1999	METHOD TO IMPROVE THE ADHESION OF A MOLDING COMPOUND TO A SEMICONDUCTOR CHIP COMPRISED WITH COPPER DAMASCENE STRUCTURES	JANG, SYUN-MING
<u>09418031</u>	<u>6734110</u>	150	10/14/1999	DAMASCENE METHOD EMPLOYING COMPOSITE ETCH STOP LAYER	JANG, SYUN-MING
<u>09409888</u>	<u>6143673</u>	150	10/01/1999	METHOD FOR FORMING GAP FILLING SILICON OXIDE INTERMETAL DIELECTRIC (IMD) LAYER FORMED EMPLOYING OZONE-TEOS	JANG, SYUN-MING
<u>09407109</u>	<u>6297162</u>	150	09/27/1999	METHOD TO REDUCE SILICON OXYNITRIDE ETCH RATE IN A SILICON OXIDE DRY ETCH	JANG, SYUN-MING
<u>09385754</u>	<u>6423625</u>	150	08/30/1999	METHOD OF IMPROVING THE BONDABILITY BETWEEN AU WIRES AND CU BONDING PADS	JANG, SYUN-MING

<u>09378496</u>	<u>6261957</u>	150	08/20/1999	SELF-PLANARIZED GAP-FILLING BY HDPCVD FOR SHALLOW TRENCH ISOLATION	JANG, SYUN-MING
<u>09378459</u>	<u>6362093</u>	150	08/20/1999	DUAL DAMASCENE METHOD EMPLOYING SACRIFICIAL VIA FILL LAYER	JANG, SYUN-MING
<u>09347910</u>	<u>6180543</u>	150	07/06/1999	METHOD OF GENERATING TWO NITROGEN CONCENTRATION PEAK PROFILES IN GATE OXIDE	JANG, SYUN-MING
<u>09336801</u>	<u>6495478</u>	150	06/21/1999	REDUCTION OF SHRINKAGE OF POLY(ARYLENE ETHER) FOR LOW-K IMD	JANG, SYUN-MING
<u>09332379</u>	<u>6176141</u>	150	06/14/1999	METHOD FOR STUD PULL TEST FOR FILM FORMED ON SEMICONDUCTOR DEVICE	JANG, SYUN-MING
<u>09320757</u>	<u>6239023</u>	150	05/27/1999	METHOD TO REDUCE THE DAMAGES OF COPPER LINES	JANG, SYUN-MING
<u>09318958</u>	<u>6319784</u>	150	05/26/1999	USING HIGH TEMPERATURE H2 ANNEAL TO RECRYSTALLIZE S/D AND REMOVE NATIVE OXIDE SIMULTANEOUSLY	JANG, SYUN-MING
<u>09318957</u>	<u>6228780</u>	150	05/26/1999	NON-SHRINKABLE PASSIVATION SCHEME FOR METAL EM IMPROVEMENT	JANG, SYUN-MING
<u>09310776</u>	<u>6043152</u>	150	05/14/1999	METHOD TO REDUCE METAL DAMAGE IN THE HDP-CVD PROCESS BY USING A SACRIFICIAL DIELECTRIC FILM	JANG, SYUN-MING
<u>09304302</u>	<u>6589872</u>	150	05/03/1999	THE USE OF LOW-HIGH SLURRY FLOW TO ELIMINATE COPPER LINE DAMAGES	JANG, SYUN-MING
<u>09303836</u>	Not Issued	161	05/03/1999	METHOD TO AVOID METAL SIDE WALL ATTACK FROM F IN HDP-FSG PROCESS	JANG, SYUN-MING
<u>09292361</u>	<u>6197669</u>	150	04/15/1999	REDUCTION OF SURFACE DEFECTS ON AMORPHOUS SILICON GROWN BY A LOW-TEMPERATURE, HIGH PRESSURE LPCVD PROCESS	JANG, SYUN-MING
<u>09285915</u>	<u>6503818</u>	150	04/02/1999	DELAMINATION RESISTANT MULTI-LAYER COMPOSITE DIELECTRIC LAYER EMPLOYING LOW DIELECTRIC CONSTANT DIELECTRIC MATERIAL	JANG, SYUN-MING
<u>09268542</u>	<u>6114253</u>	150	03/15/1999	VIA PATTERNING FOR POLY (ARYLENE ETHER) USED AS AN INTER-METAL DIELECTRIC	JANG, SYUN-MING
<u>09266374</u>	<u>6245682</u>	150	03/11/1999	REMOVAL OF SION ARC FILM AFTER POLY PHOTO AND ETCH	JANG, SYUN-MING

09252866	6180540	150	02/18/1999	METHOD FOR FORMING A STABILIZED FLUOROSILICATE GLASS LAYER	JANG, SYUN-MING
09252337	6211098	150	02/18/1999	WET OXIDATION METHOD FOR FORMING SILICON OXIDE DIELECTRIC LAYER	JANG, SYUN-MING
09244879	6010948	150	02/05/1999	SHALLOW TRENCH ISOLATION PROCESS EMPLOYING A BPSG TRENCH FILL	JANG, SYUN-MING
08620182	5904573	150	03/22/1996	PE-TEOS PROCESS	JANG, SYUN-MING
08616852	5622894	150	03/15/1996	PROCESS TO MINIMIZE A SEAM IN TUNGSTEN FILLED CONTACT HOLES	JANG, SYUN-MING
08559051	5552344	150	11/16/1995	NON-ETCHBACK SELF-ALIGNED VIA SIZE REDUCTION METHOD EMPLOYING OZONE ASSISTED CHEMICAL VAPOR DEPOSITED SILICON OXIDE	JANG, SYUN-MING
08507537	Not Issued	161	07/26/1995	MULTI-COATING METHOD YIELDING SILICON OXIDE INSULATING LAYER	JANG, SYUN-MING
08507140	Not Issued	168	07/26/1995	MULTI-COATING METHOD FOR SILICON OXIDE INSULATING LAYER	JANG, SYUN-MING

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